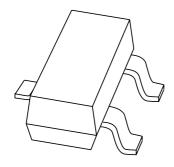
DISCRETE SEMICONDUCTORS

DATA SHEET



BCV27; BCV47 NPN Darlington transistors

Product specification Supersedes data of 1997 Sep 04 1999 Apr 08





NPN Darlington transistors

BCV27; **BCV47**

FEATURES

- Medium current (max. 500 mA)
- Low voltage (max. 60 V)
- High DC current gain (min. 20000).

APPLICATIONS

• Preamplifier input applications.

DESCRIPTION

NPN Darlington transistor in a SOT23 plastic package. PNP complements: BCV26 and BCV46.

MARKING

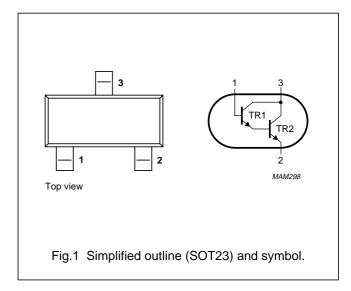
TYPE NUMBER	MARKING CODE ⁽¹⁾
BCV27	FF*
BCV47	FG*

Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BCV27		_	40	V
	BCV47		_	80	V
V _{CES}	collector-emitter voltage	open base			
	BCV27		_	30	V
	BCV47		_	60	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
I _C	collector current (DC)		_	500	mA
I _{CM}	peak collector current		_	800	mA
I _B	base current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN Darlington transistors

BCV27; BCV47

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

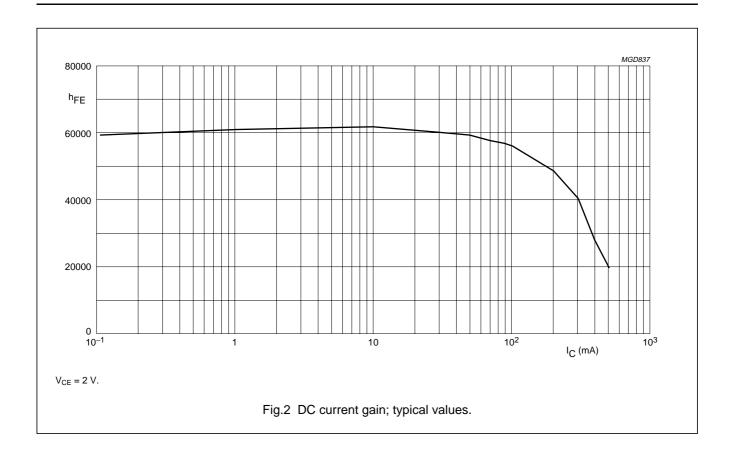
CHARACTERISTICS

 T_{amb} = 25 $^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current					
	BCV27	$I_E = 0; V_{CBO} = 30 \text{ V}$	_	_	100	nA
	BCV47	$I_E = 0; V_{CBO} = 60 \text{ V}$	_	_	100	nA
I _{EBO}	emitter cut-off current	I _E = 0; V _{EB} = 10 V	_	_	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; (see Fig.2)				
	BCV27	$I_C = 1 \text{ mA}$	4 000	_	-	
		I _C = 10 mA	10000	_	-	
		I _C = 100 mA	20000	_	-	
	DC current gain	V _{CE} = 5 V; (see Fig.2)				
	BCV47	I _C = 1 mA	2000	_	-	
		I _C = 10 mA	4 000	_	-	
		I _C = 100 mA	10000	_	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 0.1 \text{ mA}$	_	_	1	V
V _{BEsat}	base-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 0.1 \text{ mA}$	_	_	1.5	٧
V _{BEon}	base-emitter on-state voltage	$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$	_	_	1.4	٧
f _T	transition frequency	$I_C = 30 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	_	220	_	MHz

NPN Darlington transistors

BCV27; BCV47



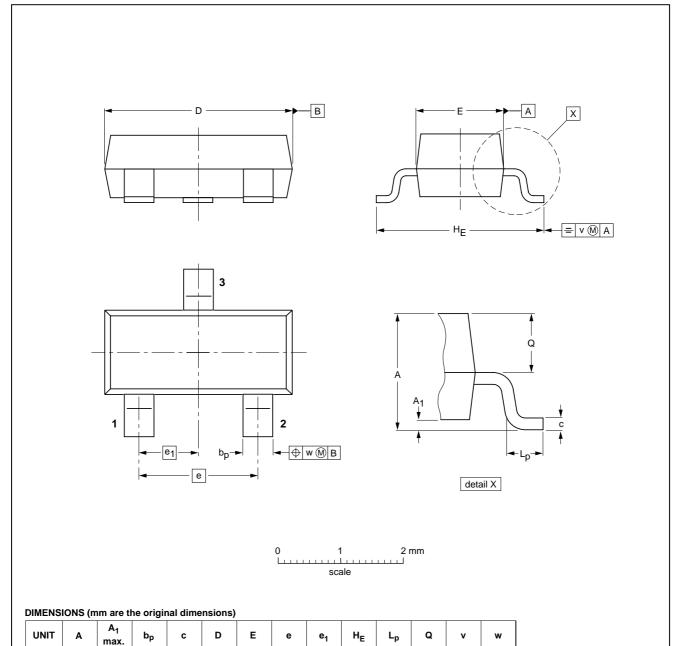
NPN Darlington transistors

BCV27; BCV47

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



OUTLINE	REFERENCES		EUROPEAN	ICCUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DATE	
SOT23						97-02-28

1.9

2.5 2.1 0.45 0.15 0.55 0.45

0.1

1999 Apr 08 5

0.48 0.38

0.1

3.0 2.8

0.15

0.09

1.1 0.9

mm

NPN Darlington transistors

BCV27; BCV47

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

NPN Darlington transistors

BCV27; BCV47

NOTES

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,

Tel. +61 2 9805 4455, Fax. +61 2 9805 4466 **Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,

220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

Belgium: see The Netherlands **Brazil:** see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,

51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 68 9211, Fax. +359 2 68 9102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,

Tel. +1 800 234 7381, Fax. +1 800 943 0087

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,

72 Tat Chee Avenue, Kowloon Tong, HONG KONG,

Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America
Czech Republic: see Austria

Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V,

Tel. +45 33 29 3333, Fax. +45 33 29 3905 **Finland:** Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615 800, Fax. +358 9 6158 0920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,

Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,

Tel. +49 40 2353 60, Fax. +49 40 2353 6300

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,

Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division,

Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510, Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14, Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007 Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,

20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557 **Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,

TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5077 **Korea:** Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,

Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,

Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,

Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,

Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,

Tel. +64 9 849 4160, Fax. +64 9 849 7811 **Norway:** Box 1, Manglerud 0612, OSLO, Tel. +47 22 74 8000, Fax. +47 22 74 8341

Pakistan: see Singapore

Philippines: Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: UI. Lukiska 10, PL 04-123 WARSZAWA, Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain Romania: see Italy

Russia: Philips Russia, UI. Usatcheva 35A, 119048 MOSCOW,

Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762,

Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,

2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,

Tel. +27 11 470 5911, Fax. +27 11 470 5494 **South America:** Al. Vicente Pinzon, 173, 6th floor,

04547-130 SÃO PAULO, SP, Brazil, Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22, 08007 BARCELONA, Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,

Tel. +46 8 5985 2000, Fax. +46 8 5985 2745 **Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH,

Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1, TAIPEI, Taiwan Tel. +886 2 2134 2886, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,

209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260, Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,

Tel. +90 212 279 2770, Fax. +90 212 282 6707

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,

252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes, MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421 United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,

Tel. +1 800 234 7381, Fax. +1 800 943 0087

Uruguay: see South America **Vietnam:** see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,

Tel. +381 11 62 5344, Fax.+381 11 63 5777

For all other countries apply to: Philips Semiconductors, International Marketing & Sales Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

© Philips Electronics N.V. 1999 SCA63

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands 115002/00/04/pp8 Date of release: 1999 Apr 08 Document order number: 9397 750 05551



Internet: http://www.semiconductors.philips.com





